

NUP2115L, SZNUP2115L

ESD Protection Diode

Low Capacitance ESD Protection for High Speed Data

The SZ/NUP2115L has been designed to protect the FlexRay transceiver from ESD and other harmful transient voltage events. This device provides bidirectional protection for each data line with a single compact SOT-23 package, giving the system designer a low cost option for improving system reliability and meeting stringent EMI requirements.

Features

- 200 W Peak Power Dissipation per Line (8/20 μ s Waveform)
- Diode Capacitance Matching
- Low Reverse Leakage Current (< 100 nA)
- Low Capacitance High-Speed FlexRay Data Rates
- IEC Compatibility:
 - IEC 61000-4-2 (ESD): Level 4
 - IEC 61000-4-4 (EFT): 50 A – 5/50 ns
 - IEC 61000-4-5 (Lighting) 3.0 A (8/20 μ s)
- ISO 7637-1, Nonrepetitive EMI Surge Pulse 2, 8.0 A (1/50 μ s)
- ISO 7637-3, Repetitive Electrical Fast Transient (EFT) EMI Surge Pulses, 50 A (5/50 ns)
- Flammability Rating UL 94 V-0
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Devices

Applications

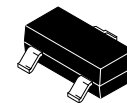
- Automotive Networks
 - ◆ FlexRay Bus



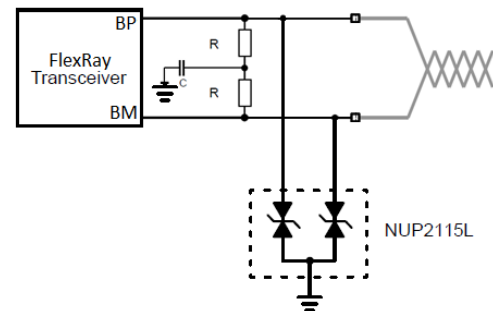
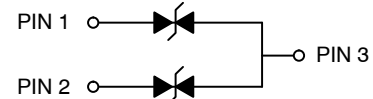
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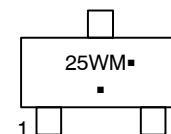
SOT-23 DUAL BIDIRECTIONAL VOLTAGE SUPPRESSOR 200 W PEAK POWER



SOT-23
CASE 318
STYLE 27



MARKING DIAGRAM



25W = Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

NUP2115L, SZNUP2115L

MAXIMUM RATINGS (T_J = 25°C, unless otherwise specified)

| Symbol | Rating | Value | Unit |
|----------------|--|------------|------|
| PPK | Peak Power Dissipation, 8 x 20 μs Double Exponential Waveform (Note 1) | 200 | W |
| T _J | Operating Junction Temperature Range | -55 to 150 | °C |
| T _J | Storage Temperature Range | -55 to 150 | °C |
| T _L | Lead Solder Temperature (10 s) | 260 | °C |
| ESD | Human Body Model (HBM) | 8.0 | kV |
| | Machine Model (MM) | 400 | V |
| | IEC 61000-4-2 Specification (Contact) | 30 | kV |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Non-repetitive current pulse per Figure 1.

ELECTRICAL CHARACTERISTICS (T_J = 25°C, unless otherwise specified)

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Unit |
|------------------|----------------------------|--|------|------|------|------|
| V _{RWM} | Reverse Working Voltage | (Note 2) | 24 | - | - | V |
| V _{BR} | Breakdown Voltage | I _T = 1 mA (Note 3) | 26.2 | - | 32 | V |
| I _R | Reverse Leakage Current | V _{RWM} = 24 V | - | 15 | 100 | nA |
| V _C | Clamping Voltage | I _{PP} = 1 A (8/20 μs Waveform) (Note 4) | - | 33.4 | 36.6 | V |
| V _C | Clamping Voltage | I _{PP} = 3 A (8/20 μs Waveform) (Note 4) | - | 44 | 50 | V |
| I _{PP} | Maximum Peak Pulse Current | 8/20 μs Waveform (Note 4) | - | - | 3.0 | A |
| C _J | Capacitance | V _R = 0 V, f = 1 MHz (Line to GND) | - | - | 10 | pF |
| ΔC | Diode Capacitance Matching | V _R = 0 V, 5 MHz (Note 5) | - | 0.1 | 2 | % |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Surge protection devices are normally selected according to the working peak reverse voltage (V_{RWM}), which should be equal or greater than the DC or continuous peak operating voltage level.
3. V_{BR} is measured at pulse test current I_T.
4. Pulse waveform per Figure 1.
5. ΔC is the percentage difference between C_J of lines 1 and 2 measured according to the test conditions given in the electrical characteristics table.

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|---------------|---------------------|-----------------------|
| NUP2115LT1G | SOT-23 (Pb-Free) | 3,000 / Tape & Reel |
| SZNUP2115LT1G | SOT-23 (Pb-Free) | 3,000 / Tape & Reel |
| NUP2115LT3G | SOT-23 (Pb-Free) | 10,000 / Tape & Reel |
| SZNUP2115LT3G | SOT-23 (Pb-Free) | 10,000 / Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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TYPICAL PERFORMANCE CURVES

($T_J = 25^\circ\text{C}$ unless otherwise noted)

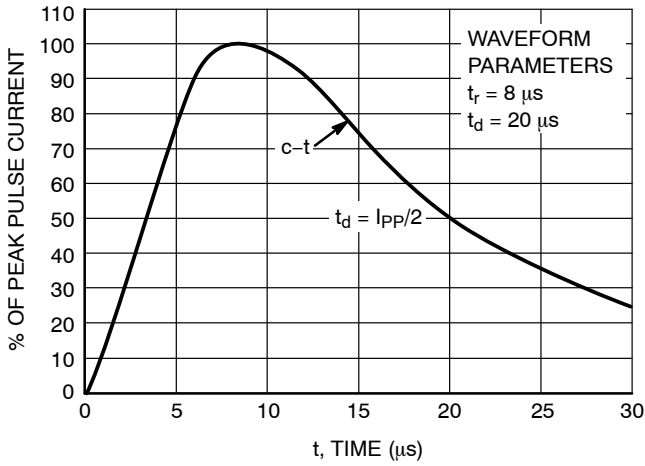


Figure 1. Pulse Waveform, $8 \times 20 \mu\text{s}$

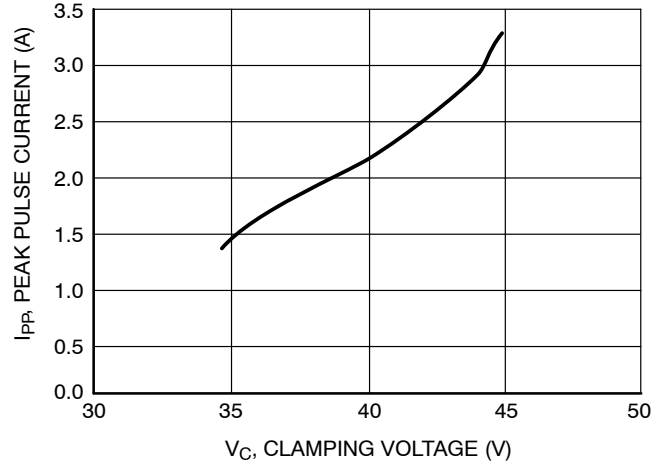


Figure 2. Clamping Voltage vs Peak Pulse Current

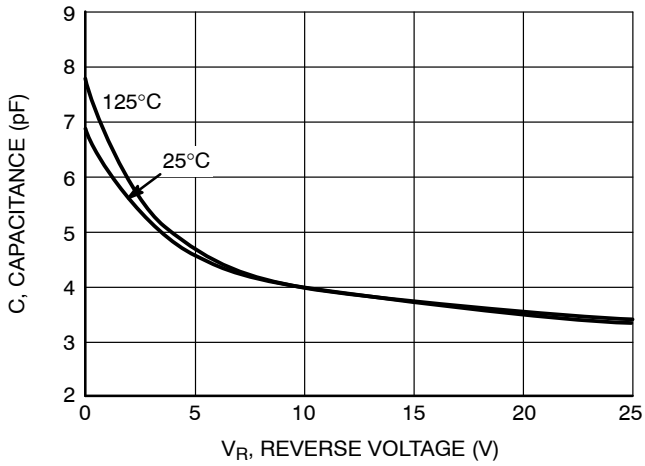


Figure 3. Typical Junction Capacitance vs Reverse Voltage

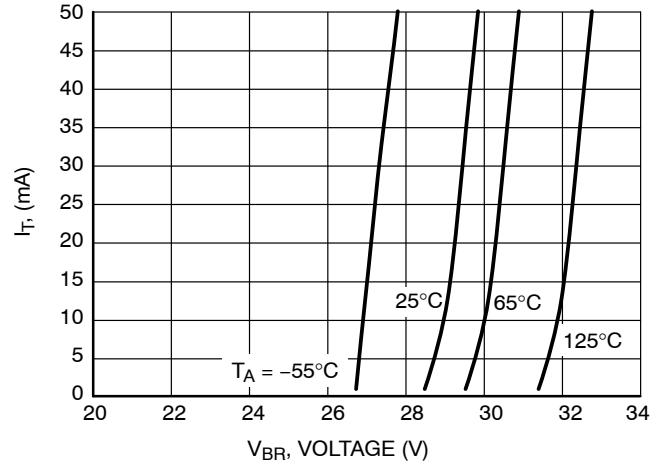


Figure 4. V_{BR} versus I_T Characteristics

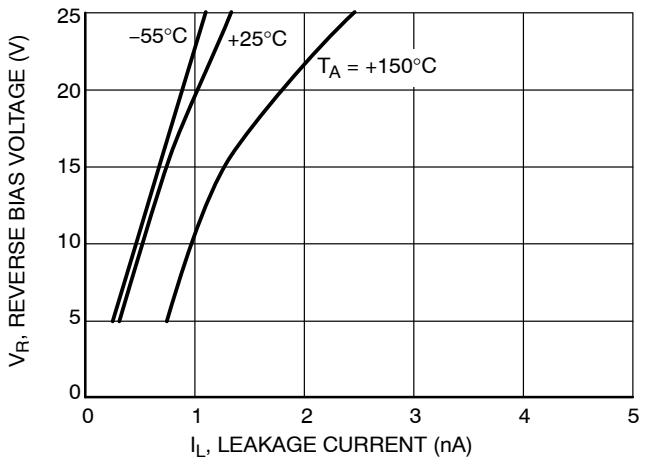


Figure 5. I_R versus Temperature Characteristics

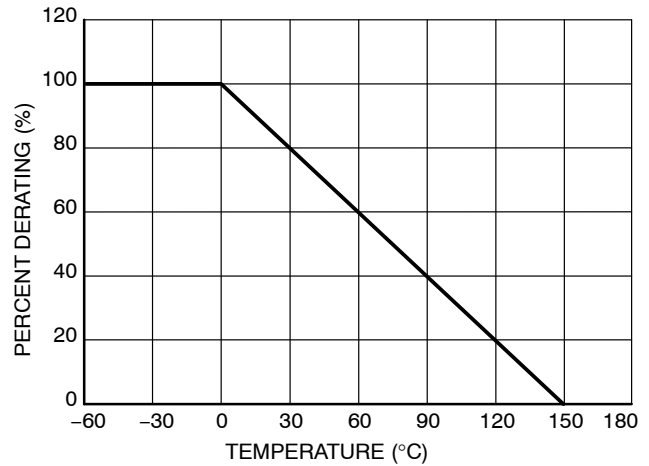


Figure 6. Temperature Power Dissipation Derating

APPLICATIONS

Surge protection diodes provide a low cost solution to conducted and radiated Electromagnetic Interference (EMI) and Electrostatic Discharge (ESD) noise problems. The noise immunity level and reliability of FlexRay transceivers can be easily increased by adding external surge protection diodes to prevent transient voltage failures.

The NUP2115L provides a surge protection solution for FlexRay data communication lines. The NUP2115L is a dual bidirectional surge protection device in a compact SOT-23 package. This device is based on Zener technology that optimizes the active area of a PN junction to provide robust protection against transient EMI surge voltage and ESD.

Surge Protection Diode Protection Circuit

Surge protection diodes provide protection to a transceiver by clamping a surge voltage to a safe level. surge protection diodes have high impedance below and low impedance above their breakdown voltage. A surge protection Zener diode has its junction optimized to absorb the high peak energy of a transient event, while a standard Zener diode is designed and specified to clamp a steady state voltage.

Figure 7 provides an example of a dual bidirectional surge protection diode array that can be used for protection with the FlexRay network. The bidirectional array is created from four identical Zener surge protection diodes. The clamping voltage of the composite device is equal to the breakdown voltage of the diode that is reversed biased, plus the diode drop of the second diode that is forward biased.

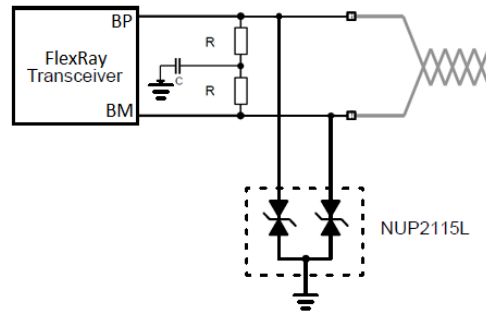


Figure 7. FlexRay Surge Protection Circuit

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SOT-23 (TO-236)
CASE 318
ISSUE AT

DATE 01 MAR 2023

SCALE 4:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| DIM | MILLIMETERS | | | INCHES | | |
|----------------|-------------|------|------|--------|-------|-------|
| | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. |
| A | 0.89 | 1.00 | 1.11 | 0.035 | 0.039 | 0.044 |
| A1 | 0.01 | 0.06 | 0.10 | 0.000 | 0.002 | 0.004 |
| b | 0.37 | 0.44 | 0.50 | 0.015 | 0.017 | 0.020 |
| c | 0.08 | 0.14 | 0.20 | 0.003 | 0.006 | 0.008 |
| D | 2.80 | 2.90 | 3.04 | 0.110 | 0.114 | 0.120 |
| E | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| e | 1.78 | 1.90 | 2.04 | 0.070 | 0.075 | 0.080 |
| L | 0.30 | 0.43 | 0.55 | 0.012 | 0.017 | 0.022 |
| L1 | 0.35 | 0.54 | 0.69 | 0.014 | 0.021 | 0.027 |
| H _E | 2.10 | 2.40 | 2.64 | 0.083 | 0.094 | 0.104 |
| T | 0° | --- | 10° | 0° | --- | 10° |

GENERIC MARKING DIAGRAM*



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS



SOT-23 (TO-236)
CASE 318
ISSUE AT

DATE 01 MAR 2023

- | | | | | | |
|---|---|---|---|---|---|
| STYLE 1 THRU 5: CANCELLED | STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR | STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR | STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE | | |
| STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE | STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE | STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE | STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE | STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE | STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE |
| STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE | STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE | STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE | STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE | STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE | STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE |
| STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN | STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT | STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE | STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE | STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE | STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION |
| STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE | STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE | | | | |

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